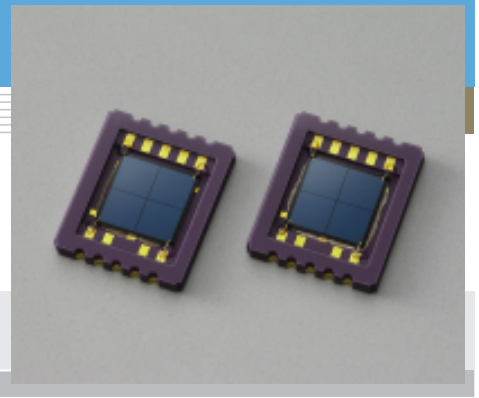


Si PIN photodiode

S8594

www.datasheet4u.com

Quadrant photodiode with slit mask for encoder



S8594 is a quadrant photodiode array with a slit mask (code strip) formed on the Si chip surface.

Features

- Quadrant photodiode with slit mask of L/S (Line/Space)=10/10 μm
- Uses a light-shielded, non-reflective black slit
- Active area: $\square 5 \text{ mm}/4$ elements (element gap: 50 μm)
- Bare chip type (window-less)

Applications

- Encoder

■ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Reverse voltage	VR Max.	30	V
Operating temperature	Topr	0 to +60 *	°C
Storage temperature	Tstg	0 to +80 *	°C

* No condensation

■ Electrical and optical characteristics (Ta=25 °C, per 1 element)

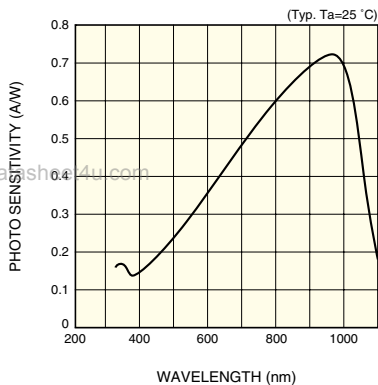
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ		-	320 to 1100	-	nm
Peak sensitivity wavelength	λ_p		-	960	-	nm
Photo sensitivity	S	$\lambda = \lambda_p$	0.60	0.72	-	A/W
Dark current	Id	VR=10 V	-	0.3	2.0	nA
Terminal capacitance	Ct	VR=10 V, f=1 MHz	-	10	-	pF
Cut-off frequency	fc	VR=10 V, RL=50 Ω $\lambda = 780 \text{ nm}$, -3 dB	-	25	-	MHz

S8594 uses a window-less package with no protection for the photodiode chip. Always take the following precautions when handling.

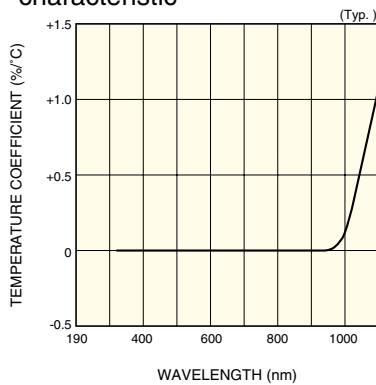
■ Handling precautions

- Handle the photodiode in a clean room.
- Never touch the photodiode chip surface and wire bonding.
- Wear dust-proof gloves and dust-proof mask.
- Use an air dust cleaner to blow dust and foreign matter away from the photodiode chip surface.
- Do not clean the photodiode by any method other than air blow.

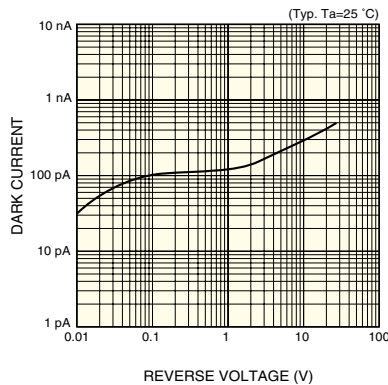
■ Spectral response



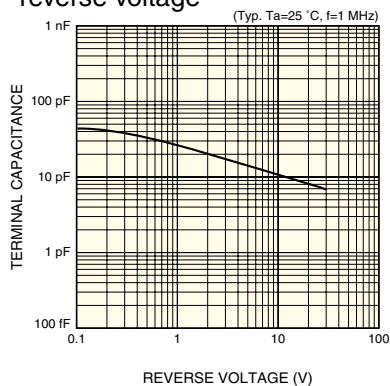
■ Photo sensitivity temperature characteristic



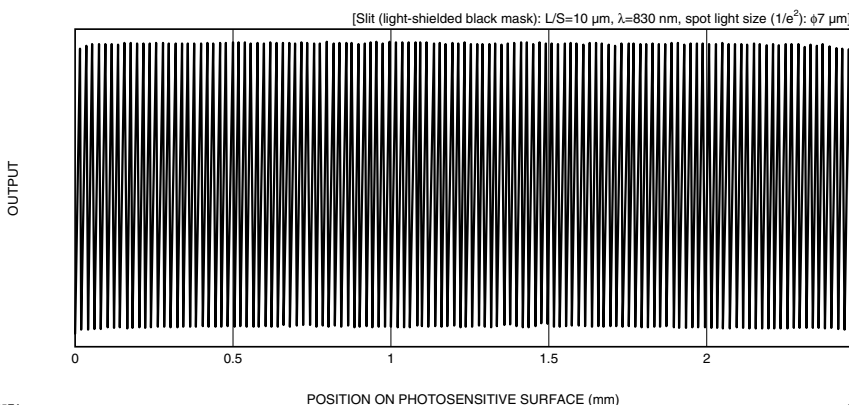
■ Dark current vs. reverse voltage



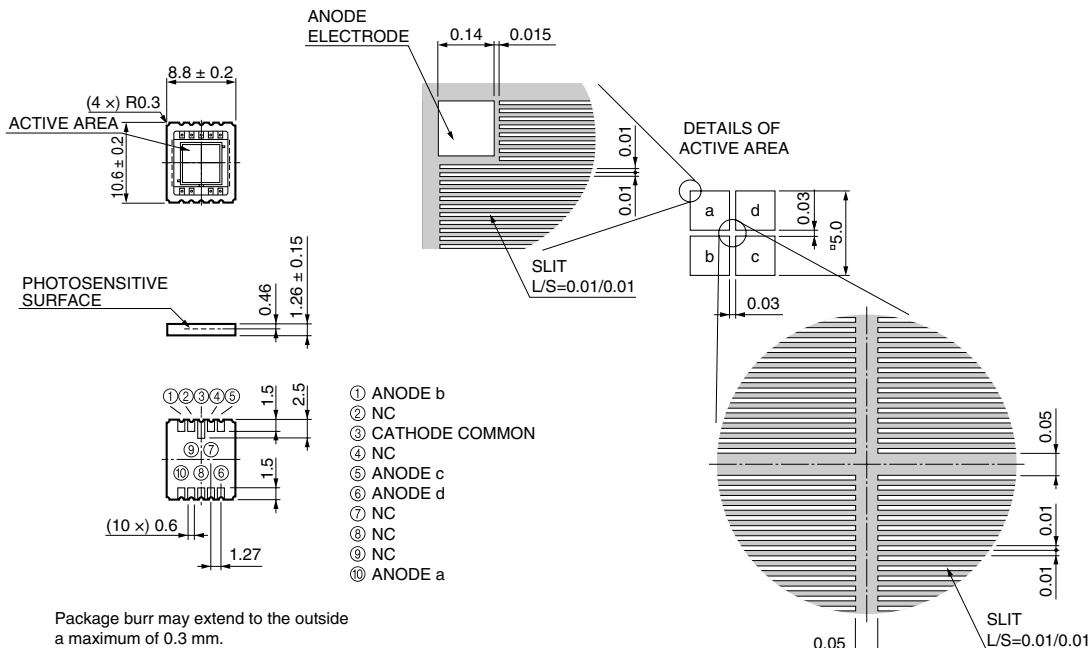
■ Terminal capacitance vs. reverse voltage



■ Photo sensitivity uniformity



■ Dimensional outline (unit: mm)



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